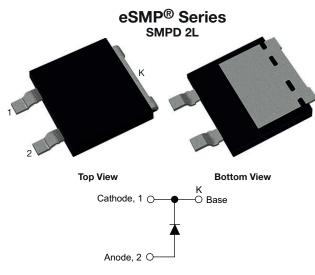
Vishay Semiconductors

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 12 A



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LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
١ _F	12 A				
V _R	650 V				
V _F at I _F at 25 °C, typ.	1.30 V				
T _J max.	175 °C				
I _R at V _R at 175 °C	20 µA				
Q _C (V _R = 400 V)	34 nC				
Package	SMPD 2L				
Circuit configuration	Single				

FEATURES

- Creepage and clearance distance 3.6 mm
 minimum
- Very low profile typical height of 1.7mm



- Majority carrier diode using Schottky technology on SiC wide band gap material
 FREE
- Improved V_F and efficiency by thin wafer technology
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- · Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^\circ\mathrm{C}$
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: SMPD 2L

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

MAXIMUM RATINGS (T _A = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		650	V		
Continuous forward current	I _F	T _M = 149 °C (DC)	12	А		
DC blocking voltage	V _{DC}		650	V		
Repetitive peak surge current	I _{FRM}	T_M = 25 °C, f = 50 Hz, square wave, DC = 25 %	61	А		
Non-repetitive peak forward surge current	I _{FSM}	$T_M = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	83	۸		
		$T_M = 110 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	74	А		
Device discipation	P _{tot} ⁽¹⁾	T _M = 25 °C	105	W		
		T _M = 110 °C	45	~ ~~		
Power dissipation	P _{tot} ⁽²⁾	T _M = 25 °C	136 W			
		T _M = 110 °C	59			
l ² t value	∫i ² dt	T _M = 25 °C	34.5	– A ² s		
		T _M = 110 °C	27			
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Stg}		-55 to +175	°C		

Notes

⁽¹⁾ Based on maximum R_{th}

⁽²⁾ Based on typical R_{th}

 $^{(3)}$ The heat generated must be less than the thermal conductivity from junction-to-ambient: dP_D/dT_J < 1/R_{θ JA}

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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	MBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
		I _F = 12 A	-	1.3	1.5		
Forward voltage	V _F	I _F = 12 A, T _J = 150 °C	-	1.50	1.85	V	
		I _F = 12 A, T _J = 175 °C	-	1.58	-		
Reverse leakage current	I _R	V _R = V _R rated	-	0.80	65	μA	
		$V_R = V_R$ rated, $T_J = 150 \text{ °C}$	-	12	150		
		V _R = V _R rated, T _J = 175 °C	-	20	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	535	-	~_	
		V _R = 400 V, f = 1 MHz	-	54	-	pF	
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	34	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. U						UNITS	
Thermal resistance, junction-to-mount	R _{thJM}		-	1.1	1.4	°C/W	
Marking device				3C12I	ED07T		

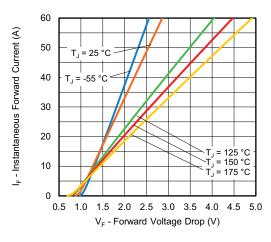


Fig. 1 - Typical Forward Voltage Drop Characteristics

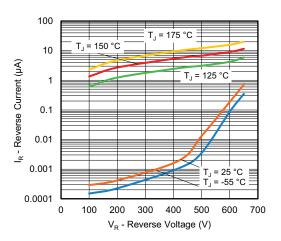


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

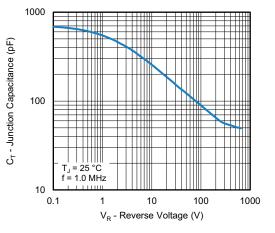


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

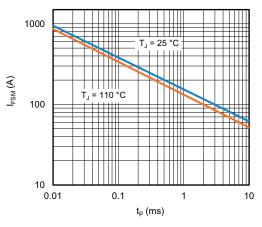


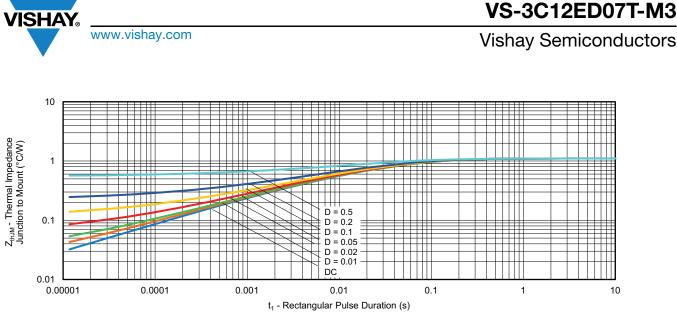
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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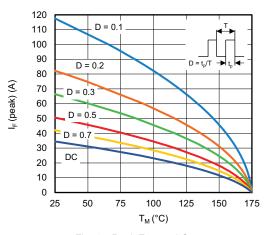


Fig. 6 - Peak Forward Current vs. Maximum Allowable Mount Temperature

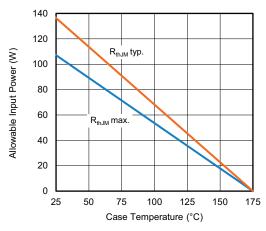


Fig. 7 - Forward Power Loss Characteristics

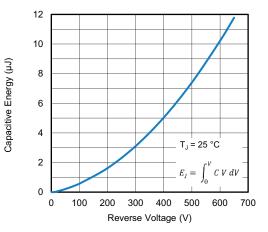


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

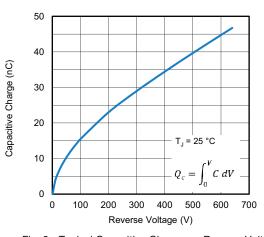


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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ORDERING INFORMATION TABLE

Device code	VS-	3C	12	Е	D	07	т	-M3	
		2	3	4	5	6	7	8	
	1	- Visł	nay Serr	nicondu	ctors pr	oduct			
	2	- 3C	3C = SiC diode, Generation 3						
	3	- Cur	Current rating (12 = 12 A)						
	4	- E=	E = single diode						
	5	- Pac	kage Sl	MPD 2L					
	6	- Volt	age rati	ng: (07	= 650 V)			
	7	- T=	T = true 2 pin						
	8	- Env	ironmer	ntal digit	:				
		-M3	3 = halog	gen-free	e, RoHS	-compli	iant, and	d termir	

ORDERING INFORMATION									
ORDERING P/N	UNIT WEIGHT	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE					
VS-3C12ED07T-M3/I	0.52 g	ļ	2000/reel	13" diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?97059					
Part marking information	www.vishay.com/doc?97105				
Packaging information	www.vishay.com/doc?88869				



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